2SK1772

Silicon N-Channel MOS FET

HITACHI

Application

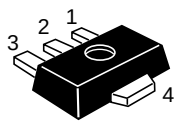
High speed power switching

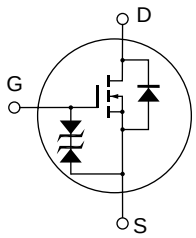
Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device - - - can be driven from 5 V source.
- Suitable for DC-DC converter, motor drive, power switch, solenoid drive

Outline

UPAK





1. Gate
2. Drain
3. Source
4. Drain

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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	1	A
Drain peak current	$I_{D(pulse)}$*[1]	2	A
Body to drain diode reverse drain current	I_{DR}	1	A
Channel dissipation	Pch*[2]	1	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

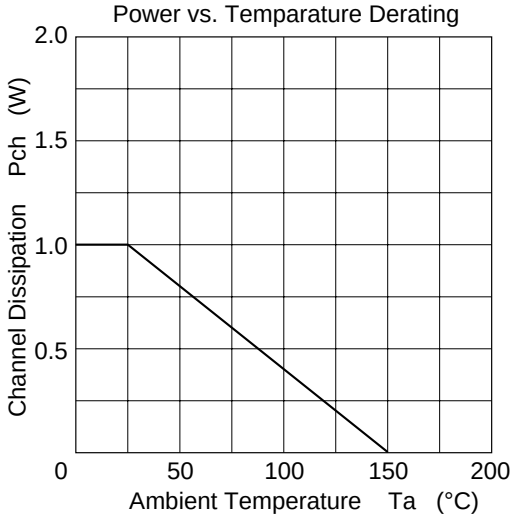
Notes 1. PW 10 µs, duty cycle 1 %
2. When using the alumina ceramic board (12.5 × 20 × 0.7mm)
3. Marking is "HY".

Electrical Characteristics (Ta = 25°C)

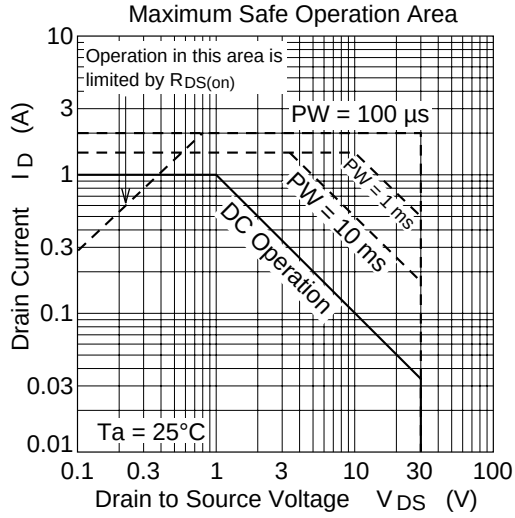
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	I_D = 10 mA, V_{GS} = 0
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	I_G = ±100 µA, V_{DS} = 0
Gate to source leak current	I_{GSS}	—	—	±10	µA	V_{GS} = ±16 V, V_{DS} = 0
Zero gate voltage drain current	I_{DSS}	—	—	50	µA	V_{DS} = 25 V, V_{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	I_D = 1 mA, V_{DS} = 10 V
Static drain to source on state resistance	$R_{DS(on)}$	—	0.4	0.6		I_D = 0.5 A V_{GS} = 10 V*[1]
		—	0.6	0.85		I_D = 0.5 A V_{GS} = 4 V*[1]
Forward transfer admittance	$\|y_{fs}\|$	0.6	1.0	—	S	I_D = 0.5 A V_{DS} = 10 V*[1]
Input capacitance	Ciss	—	85	—	pF	V_{DS} = 10 V
Output capacitance	Coss	—	65	—	pF	V_{GS} = 0
Reverse transfer capacitance	Crss	—	20	—	pF	f = 1 MHz
Turn-on delay time	$t_{d(on)}$	—	10	—	ns	I_D = 0.5 A
Rise time	t_r	—	15	—	ns	V_{GS} = 10 V
Turn-off delay time	$t_{d(off)}$	—	40	—	ns	R_L = 60
Fall time	t_f	—	30	—	ns	
Body to drain diode forward voltage	V_{DF}	—	1.2	—	V	I_F = 1 A, V_{GS} = 0
Body to drain diode reverse recovery time	t_{rr}	—	30	—	ns	I_F = 1 A, V_{GS} = 0, di_F/dt = 50 A/µs

Note 1. Pulse Test

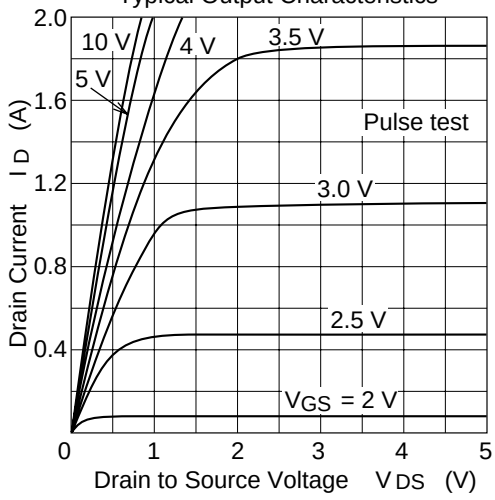
Power vs. Temparature Derating



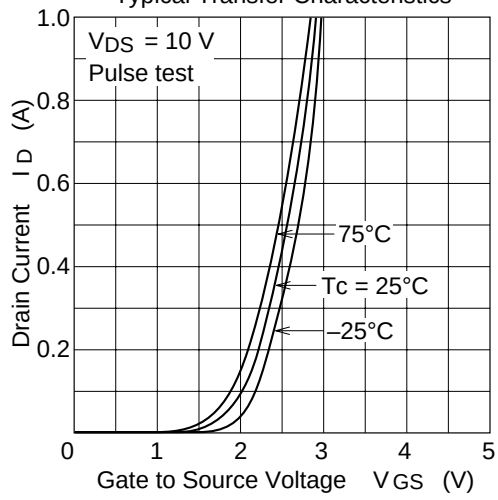
Maximum Safe Operation Area



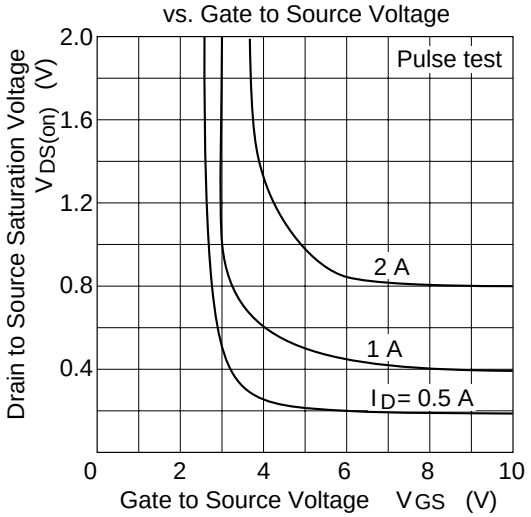
Typical Output Characteristics



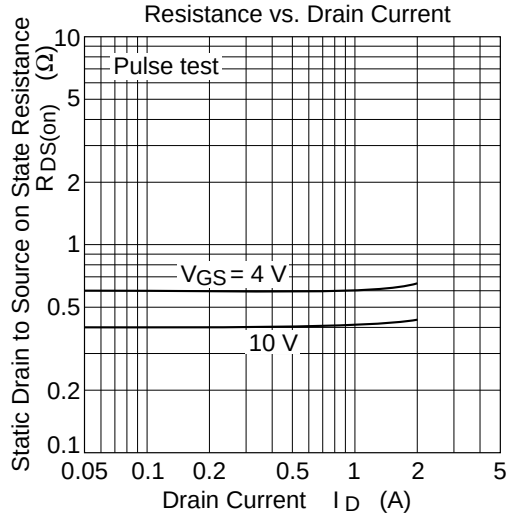
Typical Transfer Characteristics



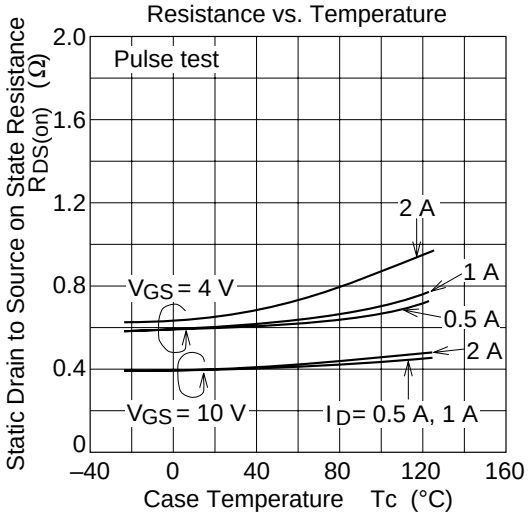
Drain to Source Saturation Voltage vs. Gate to Source Voltage



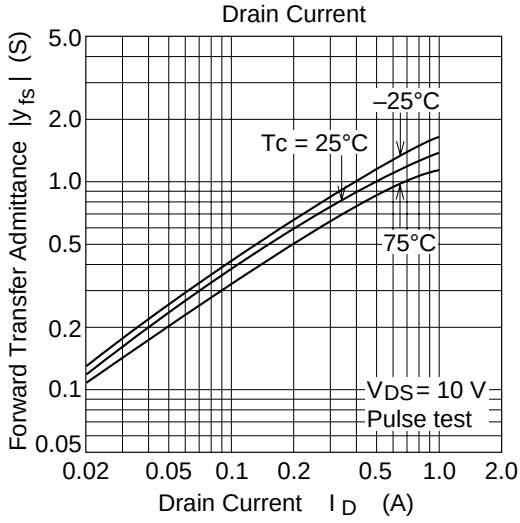
Static Drain to Source on State Resistance vs. Drain Current



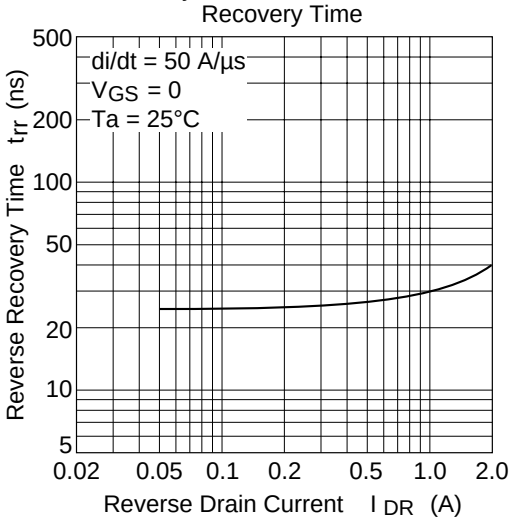
Static Drain to Source on State Resistance vs. Temperature



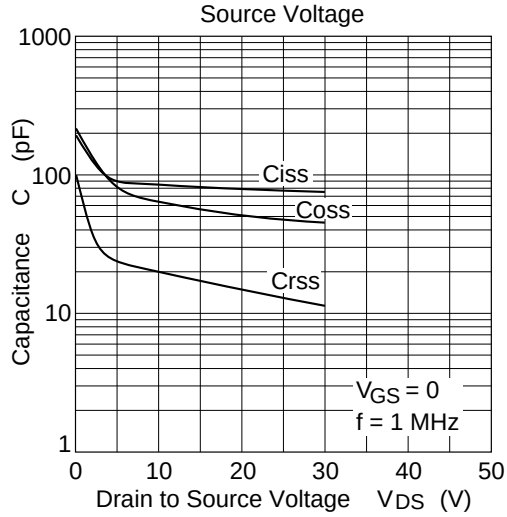
Forward Transfer Admittance vs. Drain Current



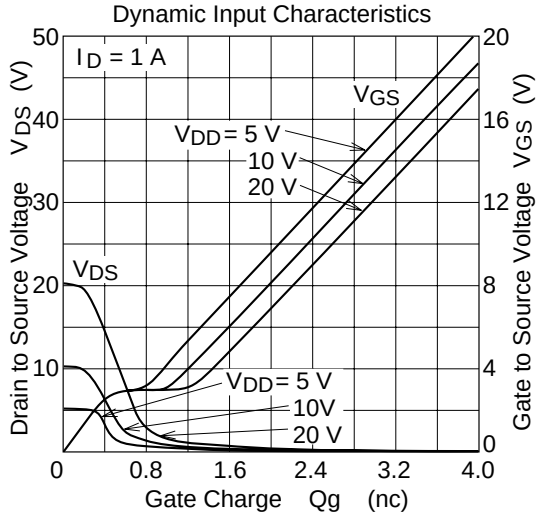
Body-Drain Diode Reverse Recovery Time



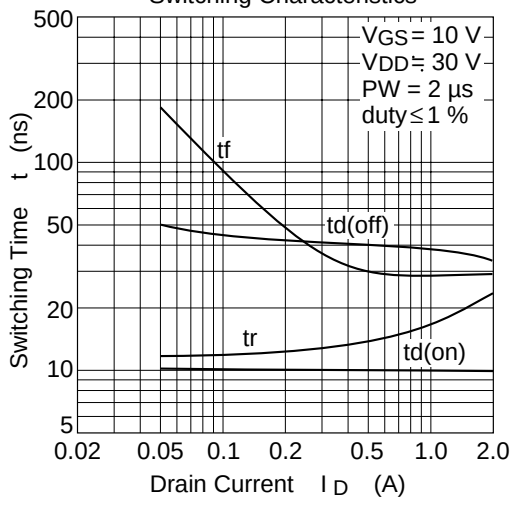
Typical Capacitance vs. Drain to Source Voltage

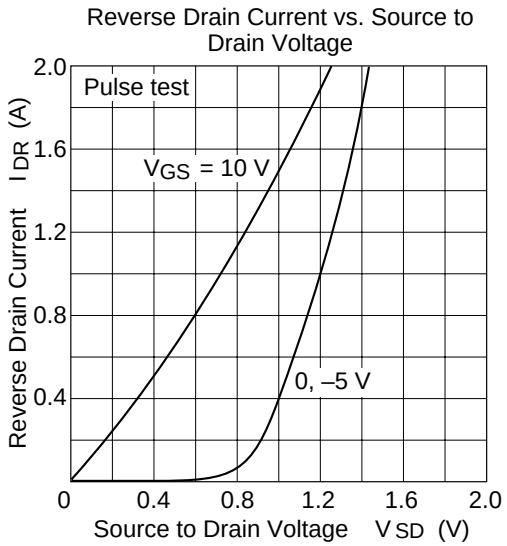


Dynamic Input Characteristics



Switching Characteristics




Reverse Drain Current vs. Source to Drain Voltage
Pulse test
V_{GS} = 10 V
0, –5 V
Reverse Drain Current I_{DR} (A)
Source to Drain Voltage V_{SD} (V)
2.0
1.6
1.2
0.8
0.4
0
0.4
0.8
1.2
1.6
2.0

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HITACHI

Hitachi, Ltd.
Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA. 94005-1835
U S A
Tel: 415-589-8300
Fax: 415-583-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Dornacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 91 80-0
Fax: 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 0628-585000
Fax: 0628-778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 0104
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 706, North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27306071